

### **BUL1102E**

# High voltage fast-switching NPN power transistor

#### **Features**

- High voltage capability
- Very high switching speed

#### **Applications**

Four lamp electronic ballast for:

- 120 V mains in push-pull configuration
- 277 V mains in half bridge current feed configuration

#### **Description**

This is a high voltage fast switching NPN power transistor manufactured in multi epitaxial planar technology. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA.

Thanks to an increased intermediate layer, it has an intrinsic ruggedness which enables the transistor to withstand a high collector current level during breakdown condition, without using the Transil<sup>TM</sup> protection usually necessary in typical converters for lamp ballast.

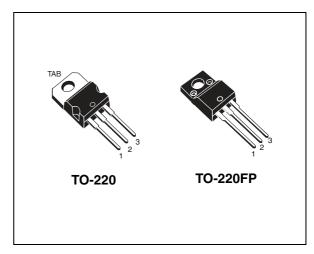


Figure 1. Internal schematic diagram

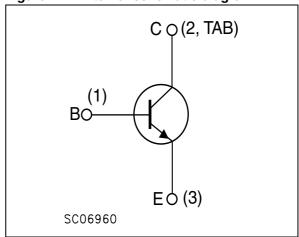


Table 1. Device summary

Order codes	Marking	Package	Packaging
BUL1102E	BUL1102E	TO-220	Tube
BUL1102EFP	BUL1102EFP	TO-220FP	Tube

### 1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage (V <sub>BE</sub> = 0)	1100	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	450	V
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> = 0)	12	V
I <sub>C</sub>	Collector current	4	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	8	Α
Ι <sub>Β</sub>	Base current	2	Α
I <sub>BM</sub>	Base peak current (t <sub>P</sub> < 5 ms)	4	Α
P <sub>TOT</sub>	BUL1102E total dissipation at $T_C = 25^{\circ}C$ BUL1102EFP total dissipation at $T_C = 25^{\circ}C$	70 30	W
V <sub>ISO</sub>	BUL1102EFP insolation withstand voltage (RMS) from all three leads to external heatsink	1500	٧
T <sub>STG</sub>	Storage temperature	-65 to 150	°C
T <sub>J</sub>	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
В.	BUL1203E thermal resistance junction-case	1.8	°C/W
$R_{thJC}$	BUL1203EFP thermal resistance junction-case	4.2	°C/W

### 2 Electrical characteristics

(T<sub>J</sub> = 25  $^{\circ}$ C; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	V <sub>CE</sub> =1100 V			100	μΑ
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 12 V			1	mA
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage (I <sub>B</sub> =0)	I <sub>C</sub> = 100 mA	450			V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	I <sub>C</sub> = 2 A I <sub>B</sub> =400 mA			1.5	٧
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	I <sub>C</sub> = 2 A I <sub>B</sub> = 400 mA			1.5	V
		I <sub>C</sub> = 250 mA V <sub>CE</sub> = 5 V	35		70	
h <sub>FE</sub> <sup>(1)</sup>	DC current gain	$I_C$ = 2 A, $V_{CE}$ = 5 V for BUL1102E $I_C$ = 2 A $V_{CE}$ = 5 V	12		20	
		for BUL1102EFP	12		23	
t <sub>s</sub>	Resistive load Storage time Fall time	$I_C = 2.5 \text{ A}$ $V_{CC} = 250 \text{ V}$ $I_{B1} = 0.5 \text{ A}$ $I_{B2} = 1 \text{ A}$ $T_P = 30 \text{ µs (see Figure 14)}$			2.5 300	μs ns
E <sub>ar</sub>	Avalanche energy	$\label{eq:L=2mH} \begin{array}{ll} \text{L} = 2 \text{ mH} & \text{C} = 1.8 \text{ nF} \\ \text{I}_{\text{BR}} \leq 2.5 \text{ A} & 25 \text{ °C} < \text{T}_{\text{C}} < 125 \text{ °C} \\ \text{(see Figure 12)} \end{array}$	6			mJ

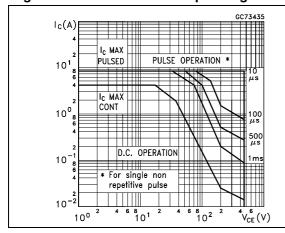
<sup>1.</sup> Pulse test: pulse duration  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.

Electrical characteristics BUL1102E

#### 2.1 Typical characteristics (curves)

Figure 2. BUL1102E safe operating area

Figure 3. BUL1102EFP safe operating area



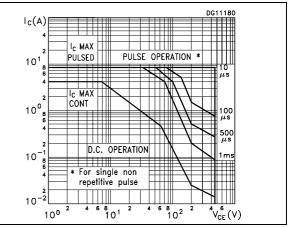
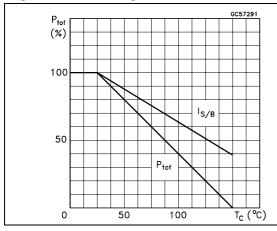


Figure 4. Derating curve

Figure 5. DC current gain  $(V_{CE} = 1 V)$ 



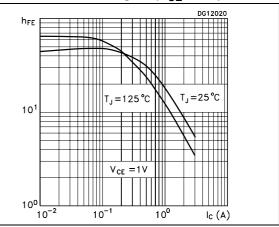
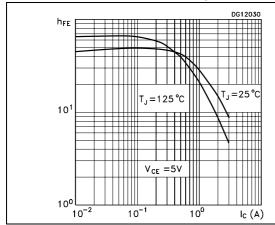


Figure 6. DC current gain  $(V_{CE} = 5 V)$ 

Figure 7. Collector emitter saturation voltage



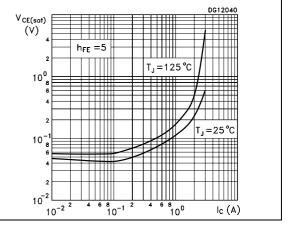
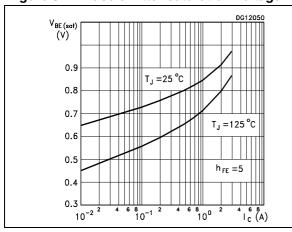


Figure 8. Base emitter saturation voltage

Figure 9. Resistive load switching times



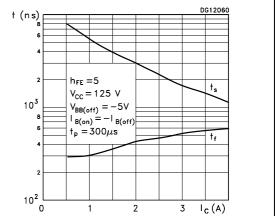
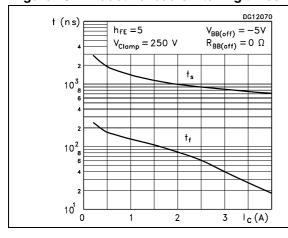
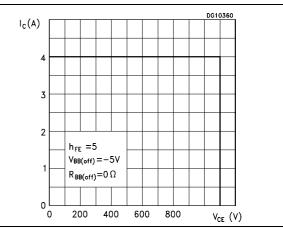


Figure 10. Inductive load switching times

Figure 11. Reverse biased SOA





Electrical characteristics BUL1102E

Figure 12. Energy rating test circuit

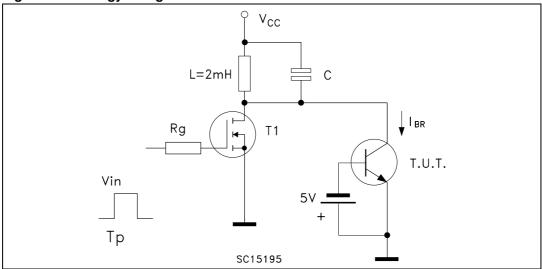


Figure 13. Inductive load switching test circuit

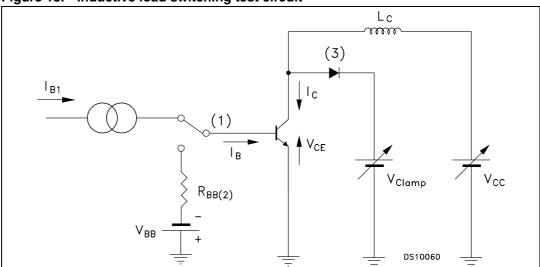
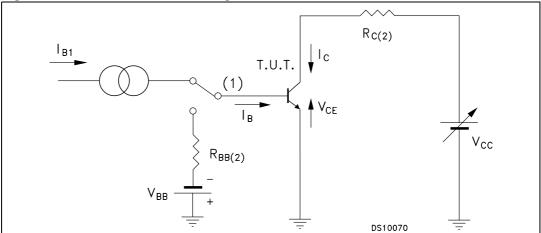


Figure 14. Resistive load switching test circuit



### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

Table 5. TO-220 type A mechanical data

Dim.	mm		
	Min.	Тур.	Max.
Α	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
С	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 15. TO-220 type A drawing

Table 6. TO-220FP mechanical data

Dim.		mm		
	Min.	Тур.	Max.	
Α	4.4		4.6	
В	2.5		2.7	
D	2.5		2.75	
Е	0.45		0.7	
F	0.75		1	
F1	1.15		1.70	
F2	1.15		1.70	
G	4.95		5.2	
G1	2.4		2.7	
Н	10		10.4	
L2		16		
L3	28.6		30.6	
L4	9.8		10.6	
L5	2.9		3.6	
L6	15.9		16.4	
L7	9		9.3	
Dia	3		3.2	

Figure 16. TO-220FP drawing

Revision history BUL1102E

## 4 Revision history

Table 7. Document revision history

Date	Revision	Changes
17-Jan-2008	3	
24-Mar-2011	4	Inserted BUL1102EFP order code in TO-220FP package
15-Feb-2012	5	DC current gain values in Table 4 modified

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